

Features

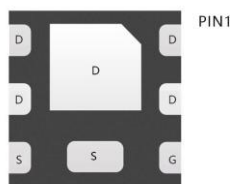
- Trench Power LV MOSFET technology
- High Power and Current handling capability
- Low Gate Charge
- Surface Mount Package

Product Summary

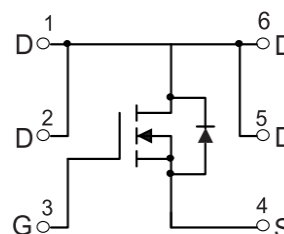
V_{DS}	$R_{DS(ON)}$ TYP	I_D
20V	10m Ω @4.5V	12A
	13m Ω @2.5V	

Application

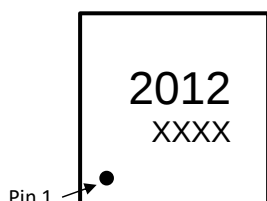
- PWM applications
- Power management
- Load switch



DFN2X2-6L view



Schematic diagram



Pin 1

2012 : Device code
 XXXX: Code
 Solid dot: Pin1 indicator

Marking and pin assignment



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	20	V
V_{GS}	Gate-Source Voltage	± 10	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 12	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 40	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 12	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 2.5	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	50	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSM2012	DFN2X2-6L	2012	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.35	--	1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =5A	--	10	15	mΩ
		V _{GS} =2.5V, I _D =5A	--	13	18	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =4V, V _{GS} =0V, f=1MHz	--	1800	--	pF
C _{OSS}	Output Capacitance		--	650	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	450	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =4V, I _D =10A, V _{GS} =5V	--	--	32	nC
Q _{gs}	Gate Source Charge		--	2.5	--	nC
Q _{gd}	Gate Drain Charge		--	6.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =4V, I _D =10A, V _{GS} =4.5V, R _G =1Ω	--	12	--	nS
t _r	Turn-on Rise Time		--	10	--	nS
t _{d(off)}	Turn-Off Delay Time		--	65	--	nS
t _f	Turn-Off Fall Time		--	20	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =10A	--	--	1.2	V

Typical Operating Characteristics

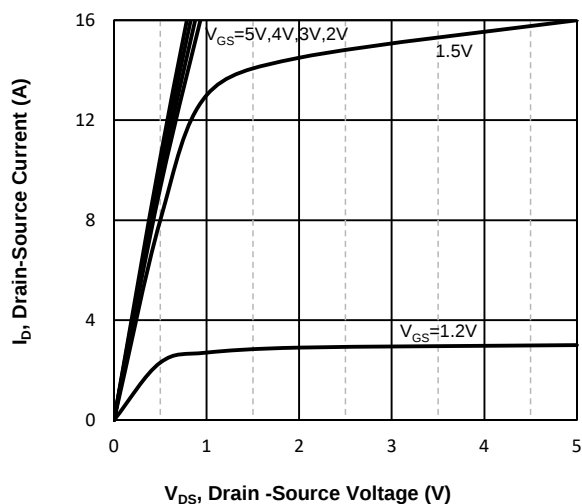


Fig1. Typical Output Characteristics

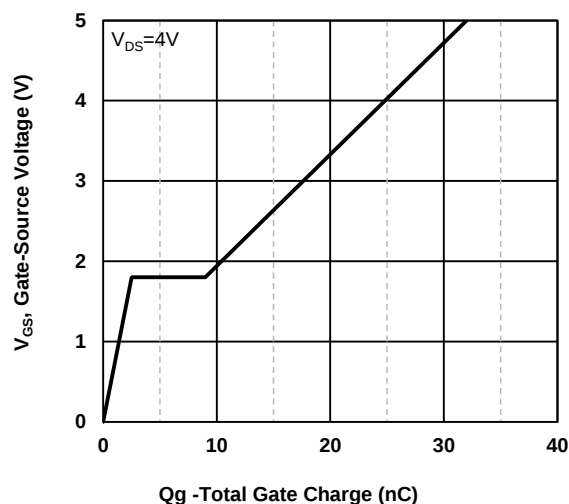


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

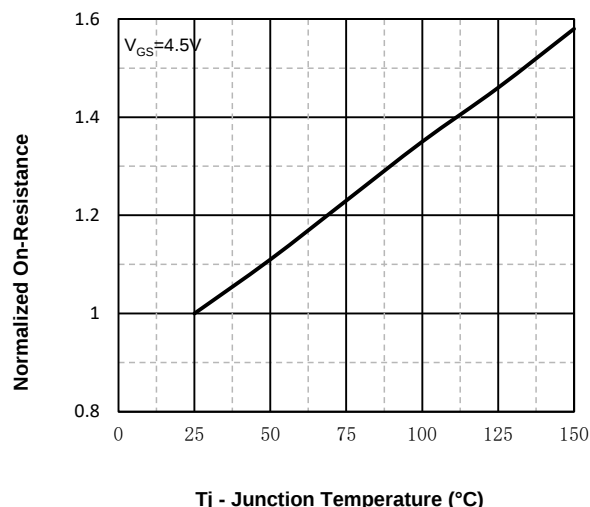


Fig3. Normalized On-Resistance Vs. Temperature

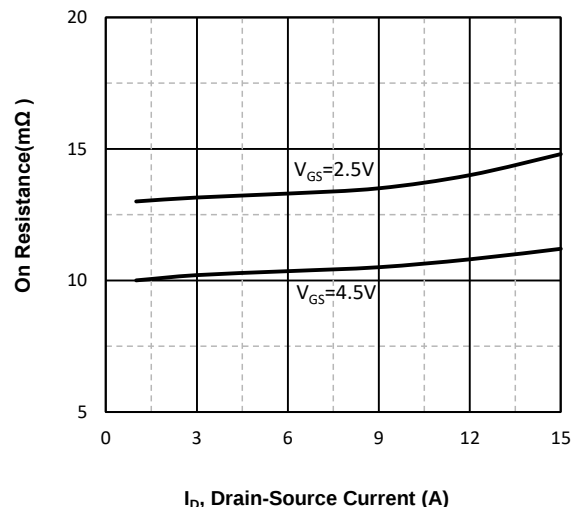


Fig4. On Resistance Vs. Drain-Source Current

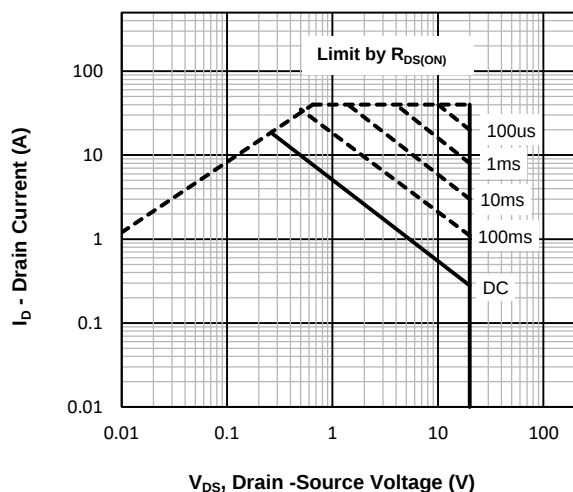


Fig5. Maximum Safe Operating Area

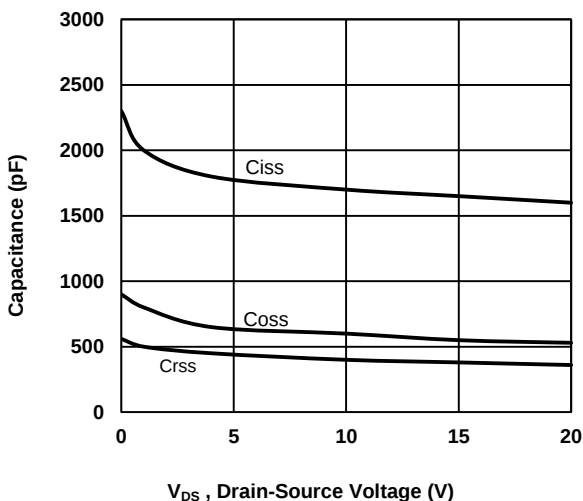
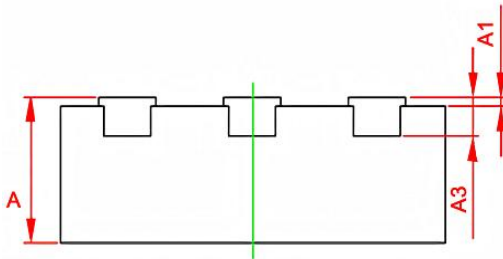
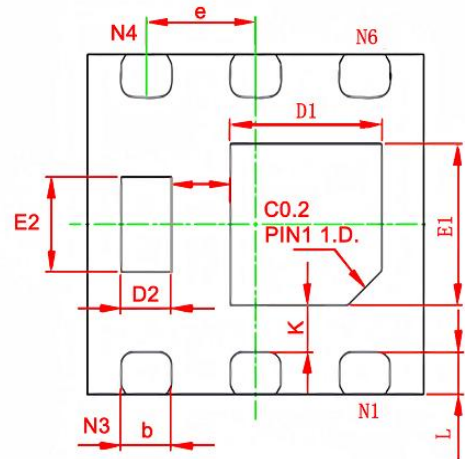
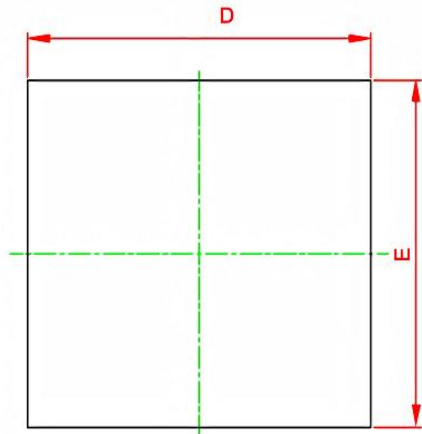


Fig6 Typical Capacitance Vs. Drain-Source Voltage

DFN2X2-6L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.600	0.700	0.023	0.027
A1	0.000	0.050	0.000	0.001
A3	0.203REF		0.007REF	
b	0.315	0.415	0.012	0.016
D	1.924	2.076	0.075	0.081
E	1.924	2.076	0.075	0.081
e	0.650TYP		0.225TYP	
L	0.224	0.376	0.008	0.014
k	0.200	-	0.007	-
E1	1.000	1.200	0.039	0.047
D1	0.900	1.100	0.035	0.043
E2	0.700	0.900	0.027	0.035
D2	0.150	0.350	0.005	0.013